Mary Ellen Zvanut

List of Publications by Year
in descending order

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51	641	706676	685536
papers	citations	14	24
		h-index	g-index

51	51	51	767
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Optical transitions of neutral Mg in Mg-doped Î²-Ga2O3. APL Materials, 2022, 10, .	2.2	9
2	Optical transitions of gallium vacancies in neutron irradiated Î²-Ga2O3. Journal of Applied Physics, 2022, 132, .	1.1	5
3	Charge trapping at Fe due to midgap levels in Ga2O3. Journal of Applied Physics, 2021, 129, .	1.1	14
4	Carbon complexes in highly C-doped GaN. Physical Review B, 2021, 104, .	1.1	18
5	Fe-related optical transitions in floating zone and Czochralski grown Î²-Ga2O3 crystals. Journal of Applied Physics, 2021, 130, .	1.1	5
6	A Deep Carbonâ€Related Acceptor Identified through Photoâ€Induced Electron Paramagnetic Resonance. Physica Status Solidi (B): Basic Research, 2020, 257, 1900593.	0.7	1
7	Optical transitions for impurities in Ga2O3 as determined by photo-induced electron paramagnetic resonance spectroscopy. Journal of Applied Physics, 2020, 127, 065704.	1.1	16
8	Small non-uniform basal crystal fields in HVPE free-standing GaN:Mg as evidenced by angular dependent and frequency-dependent EPR. Journal of Physics Condensed Matter, 2019, 31, 345702.	0.7	2
9	Optical absorption of Fe in doped Ga2O3. Journal of Applied Physics, 2019, 126, .	1.1	28
10	Photo-EPR study of compensated defects in Be-doped GaN substrates. Journal of Applied Physics, 2019, 125, .	1.1	6
11	Incorporation of Carbon in Free-Standing HVPE-Grown GaN Substrates. Journal of Electronic Materials, 2019, 48, 2226-2232.	1.0	17
12	A compensating point defect in carbon-doped GaN substrates studied with electron paramagnetic resonance spectroscopy. Journal of Applied Physics, 2018, 123, .	1.1	8
13	Charge transfer process for carbon-related center in semi-insulating carbon-doped GaN. Journal of Applied Physics, 2018, 124, .	1.1	16
14	Incorporation of Mg into thick free-standing HVPE GaN. MRS Advances, 2016, 1, 169-174.	0.5	0
15	Incorporation of Mg in Free-Standing HVPE GaN Substrates. Journal of Electronic Materials, 2016, 45, 2692-2696.	1.0	13
16	Effect of local fields on the Mg acceptor in GaN films and GaN substrates. Journal of Applied Physics, 2016, 120, .	1.1	7
17	Large Persistent Photoconductivity in Strontium Titanate at Room Temperature. Materials Research Society Symposia Proceedings, 2015, 1792, 1.	0.1	6
18	Determination of an acceptor level in bulk GaN grown by high nitrogen pressure solution method. Physica Status Solidi (B): Basic Research, 2015, 252, 923-927.	0.7	5

#	Article	IF	Citations
19	Electron paramagnetic resonance studies of bulk Mg-doped GaN grown by high nitrogen pressure solution method. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 338-340.	0.8	0
20	Reduction in the Number of Mg Acceptors with Al Concentration in Al x Ga1â^'x N. Journal of Electronic Materials, 2015, 44, 4139-4143.	1.0	1
21	The effects of Al on the neutral Mg acceptor impurity in Alx Ga1-x N. Physica Status Solidi C: Current Topics in Solid State Physics, 2015, 12, 357-360.	0.8	0
22	The effect of growth parameters on the Mg acceptor in Inx Ga1-x N:Mg and Alx Ga1-x N:Mg. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 594-597.	0.8	4
23	The source of holes in p-type InxGa1â^'xN films. Journal of Applied Physics, 2012, 112, .	1.1	1
24	Charge transfer in semi-insulating Fe-doped GaN. Journal of Applied Physics, 2012, 112, .	1.1	14
25	Passivation and activation of Mg acceptors in heavily doped GaN. Journal of Applied Physics, 2011, 110, .	1.1	17
26	Iron-related defect levels in SrTiO3 measured by photoelectron paramagnetic resonance spectroscopy. Journal of Applied Physics, 2010, 107, 083513.	1.1	15
27	Photoinduced behavior of the VCCSiâ^' pair defect in 4H-SiC grown by physical vapor transport and halide chemical vapor deposition. Journal of Applied Physics, 2009, 106, 064908.	1.1	0
28	Density of interface states, electron traps, and hole traps as a function of the nitrogen density in SiO2 on SiC. Journal of Applied Physics, 2009, 105, .	1.1	158
29	A study of vacancies and vacancy pair defects in 4H SiC grown by halide chemical vapor deposition. Journal of Materials Science: Materials in Electronics, 2008, 19, 678-681.	1.1	0
30	An annealing study of an oxygen vacancy related defect in SrTiO3 substrates. Journal of Applied Physics, 2008, 104, .	1.1	33
31	Measurements of optical cross sections of the carbon vacancy in 4H-SiC by time-dependent photoelectron paramagnetic resonance. Journal of Applied Physics, 2008, 104, 113707.	1.1	10
32	Point Defects in 4H SiC Grown by Halide Chemical Vapor Deposition. Materials Science Forum, 2007, 556-557, 473-476.	0.3	1
33	Study of Chromium Impurities in SrTiO3 by Photo-Electron Paramagnetic Resonance Spectroscopy. Materials Research Society Symposia Proceedings, 2007, 1034, 117.	0.1	1
34	A Study of Deep Defect Levels in Semi-Insulating SiC Using Optical Admittance Spectroscopy. Journal of Electronic Materials, 2007, 36, 623-628.	1.0	1
35	Electrical Measurement of the Vanadium Acceptor Level in 4H- and 6H-SiC. Materials Research Society Symposia Proceedings, 2006, 911, 6.	0.1	0
36	The effects of oxygen, nitrogen, and hydrogen annealing on Mg acceptors in GaN as monitored by electron paramagnetic resonance spectroscopy. Journal of Electronic Materials, 2005, 34, 34-39.	1.0	14

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37	Electron paramagnetic resonance of electronic-grade SiC substrates. Journal of Physics Condensed Matter, 2004, 16, R1341-R1367.	0.7	9
38	Thermal activation of Mg-doped GaN as monitored by electron paramagnetic resonance spectroscopy. Journal of Applied Physics, 2004, 95, 1884-1887.	1.1	18
39	Electron Paramagnetic Resonance Characterization of SiC. Springer Series in Materials Science, 2004, , 277-302.	0.4	1
40	Effects of high-temperature annealing on defects and impurities in As-grown semi-insulating 4H SiC. Journal of Electronic Materials, 2003, 32, 444-447.	1.0	4
41	The level position of a deep intrinsic defect in 4H-SiC studied by photoinduced electron paramagnetic resonance. Applied Physics Letters, 2002, 80, 410-412.	1.5	63
42	Activation of Mg acceptors in GaN:Mg monitored by electron paramagnetic resonance spectroscopy.. Materials Research Society Symposia Proceedings, 2002, 743, L11.59.1.	0.1	0
43	Interactions between intrinsic defects and nitrogen/boron impurities in high-resistivity 4H SiC: Electron paramagnetic resonance study. Journal of Electronic Materials, 2002, 31, 351-355.	1.0	3
44	Characterization of paramagnetic defect centers in three polytypes of dry heat treated, oxidized SiC. Journal of Applied Physics, 2000, 88, 4122.	1.1	38
45	Reduction and creation of paramagnetic centers on surfaces of three different polytypes of SiC. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1999, 17, 1627.	1.6	6
46	Characterization of the luminescence center in photo- and electroluminescent amorphous silicon oxynitride films. Journal of Applied Physics, 1999, 86, 2628-2637.	1.1	36
47	Generation and annealing characteristics of paramagnetic centers in oxidized 3C-SiC and 6H-SiC. Journal of Electronic Materials, 1999, 28, 144-147.	1.0	12
48	Effect of Varying Oxidation Parameters on the Generation of C-Dangling Bond Centers in Oxidized SiC. Materials Research Society Symposia Proceedings, 1999, 572, 51.	0.1	2
49	EPR Study of the Role of Hydrogen in the Defect Formation Upon Heat Treatment of Oxidized SiC. Materials Research Society Symposia Proceedings, 1998, 513, 433.	0.1	3
50	Ge-Related Interfacial Defects in Sige Alloy Structures. Materials Research Society Symposia Proceedings, 1995, 405, 453.	0.1	0
51	Ge-Related Interfacial Defects In SiGe Alloy Structures. Materials Research Society Symposia Proceedings, 1995, 406, 573.	0.1	0